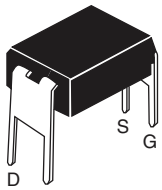
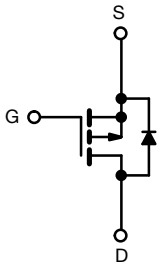
Power MOSFET

HVMDIP





P-Channel MOSFET

FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- For automatic Insertion
- End stackable
- P-channel
- 175 °C operating temperature
- Fast switching
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The 4 pin DIP package is a low cost machine-insertable case style which can be stacked in multiple combinations on standard 0.1" pin centers. The dual drain servers as a thermal link to the mounting surface for power dissipation levels up to 1 W.

PRODUCT SUMMARY		
V_{DS} (V)	-60	
$R_{DS(on)}$ (Ω)	V_{GS} = -10 V	0.50
Q_g (Max.) (nC)	12	
Q_{gs} (nC)	3.8	
Q_{gd} (nC)	5.1	
Configuration	Single	

ORDERING INFORMATION	
Package	HVMDIP
Lead (Pb)-free	IRFD9014PbF

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)					
PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V_{DS}	-60	V
Gate-source voltage			V_{GS}	± 20	
Continuous drain current	V_{GS} at 10 V	T_A = 25 °C	I_D	-1.1	A
		T_A = 100 °C		-0.80	
Pulsed drain current [a]			I_{DM}	-8.8	
Linear derating factor				0.0083	W/°C
Single pulse avalanche energy [b]			E_{AS}	140	mJ
Repetitive avalanche current [a]			I_{AR}	-1.1	A
Repetitive avalanche energy [a]			E_{AR}	0.13	mJ
Maximum power dissipation	T_A = 25 °C		P_D	1.3	W
Peak diode recovery dV/dt [c]			dV/dt	-4.5	V/ns
Operating junction and storage temperature range			T_J, T_{stg}	-55 to +175	°C
Soldering recommendations (peak temperature)	For 10 s			300[d]	

Notes

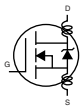
a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
b. V_{DD} = -25 V, starting T_J = 25 °C, L = 33 mH, R_g = 25 Ω, I_{AS} = -2.2 A (see fig. 12)
c. I_{SD} ≤ -6.7 A, dI/dt ≤ 90 A/µs, V_{DD} ≤ V_{DS}, T_J ≤ 175 °C
d. 1.6 mm from case

For technical questions, contact: hvm@vishay.com

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	120	°C/W

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = -250 µA		-60	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = -1 mA		-	-0.060	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA		-2.0	-	-4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -60 V, V_{GS} = 0 V		-	-	-100	µA
		V_{DS} = -48 V, V_{GS} = 0 V, T_J = 150 °C		-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = -10 V	I_D = -0.66 A[b]	-	-	0.50	Ω
Forward Transconductance	g_{fs}	V_{DS} = -25 V, I_D = -0.66 A[b]		0.70	-	-	S
Dynamic							
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = -25 V, f = 1.0 MHz, see fig. 5		-	270	-	pF
Output Capacitance	C_{oss}			-	170	-	
Reverse Transfer Capacitance	C_{rss}			-	31	-	
Total Gate Charge	Q_g	V_{GS} = -10 V	I_D = -6.7 A, V_{DS} = -48 V, see fig. 6 and 13[b]	-	-	12	nC
Gate-Source Charge	Q_{gs}			-	-	3.8	
Gate-Drain Charge	Q_{gd}			-	-	5.1	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = -30 V, I_D = -6.7 A, R_g = 24 Ω, R_D = 4.0 Ω, see fig. 10[b]		-	11	-	ns
Rise Time	t_r			-	63	-	
Turn-Off Delay Time	$t_{d(off)}$			-	10	-	
Fall Time	t_f			-	31	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.0	-	nH
Internal Source Inductance	L_S			-	6.0	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	-1.1	A
Pulsed Diode Forward Current[a]	I_{SM}			-	-	-8.8	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = -1.1 A, V_{GS} = 0 V[b]		-	-	-5.5	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = -6.7 A, dI/dt = 100 A/µs[b]		-	80	160	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	0.096	0.19	µC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)

b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %

For technical questions, contact: hvm@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

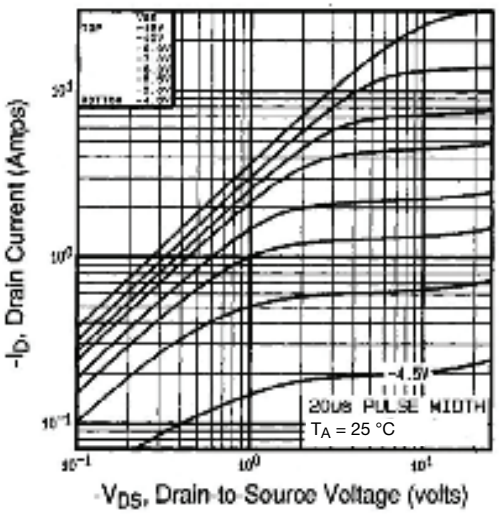


Fig. 1 - Typical Output Characteristics, T_A = 25 °C

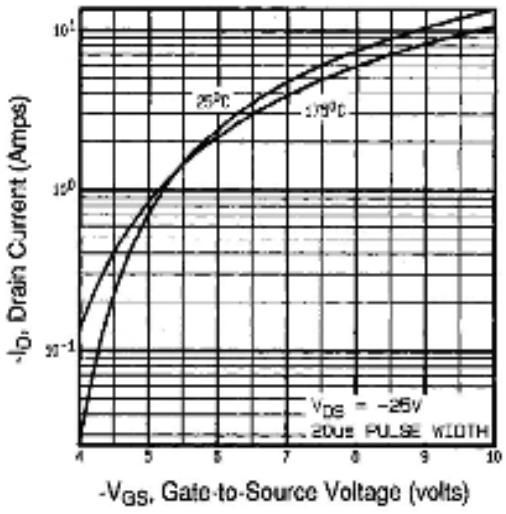


Fig. 2 - Typical Transfer Characteristics

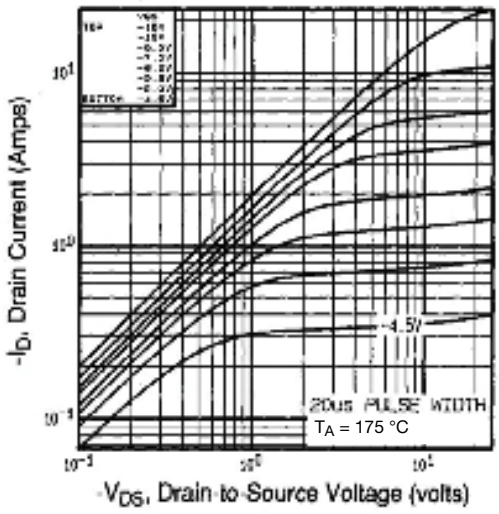


Fig. 1 - Typical Output Characteristics, T_A = 175 °C

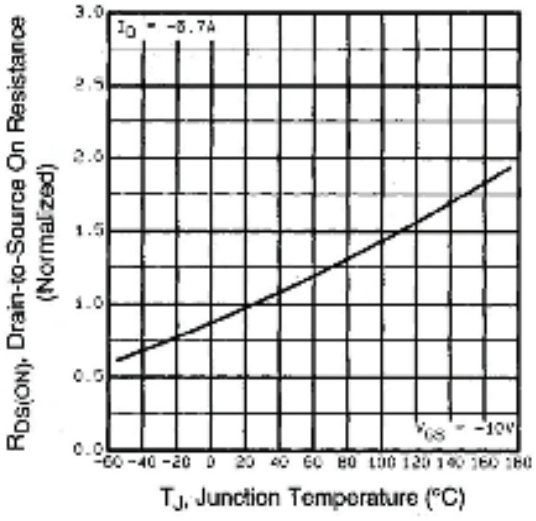


Fig. 3 - Normalized On-Resistance vs. Temperature

For technical questions, contact: hvm@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

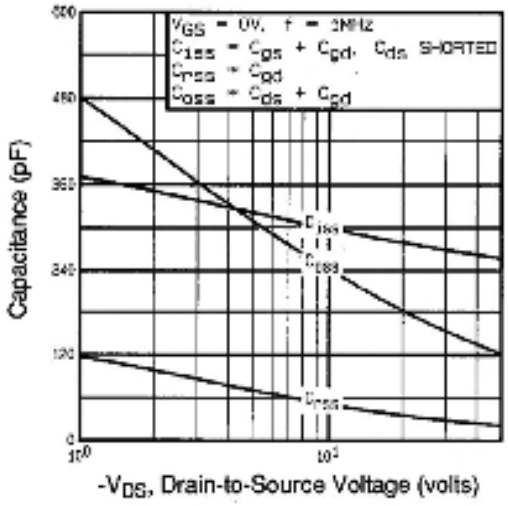


Fig. 4 - Typical Capacitance vs. Drain-to-Source Voltage

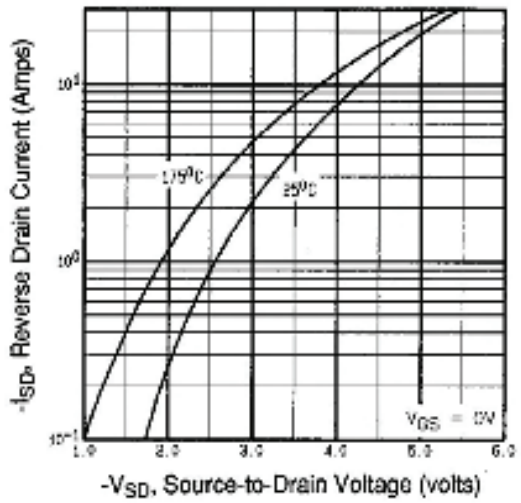


Fig. 6 - Typical Source-Drain Diode Forward Voltage

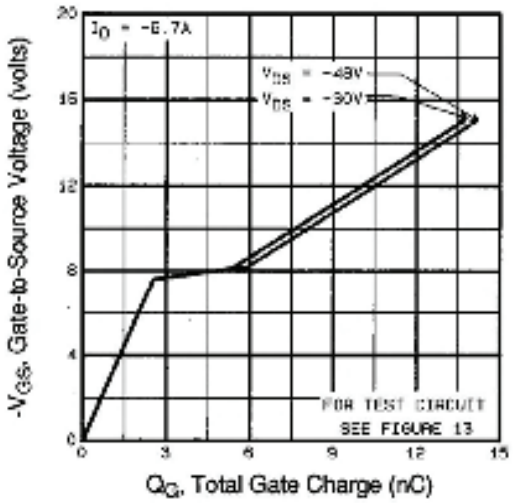


Fig. 5 - Typical Gate Charge vs. Gate-to-Source Voltage

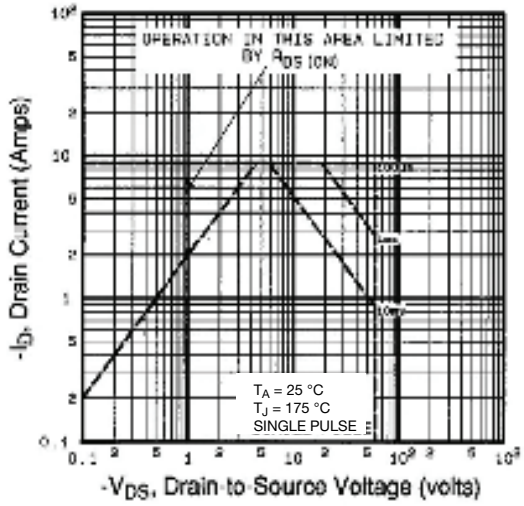


Fig. 7 - Maximum Safe Operating Area

For technical questions, contact: hvm@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

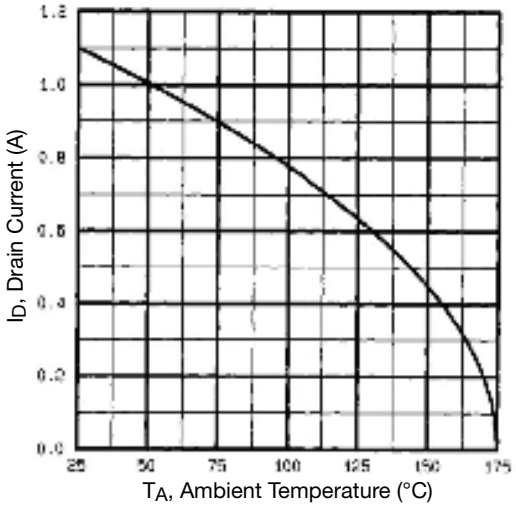


Fig. 8 - Maximum Drain Current vs. Ambient Temperature

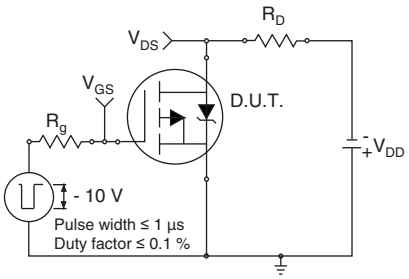


Fig. 10a - Switching Time Test Circuit

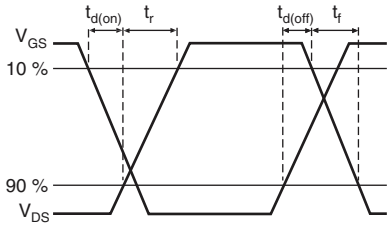


Fig. 10b - Switching Time Waveforms

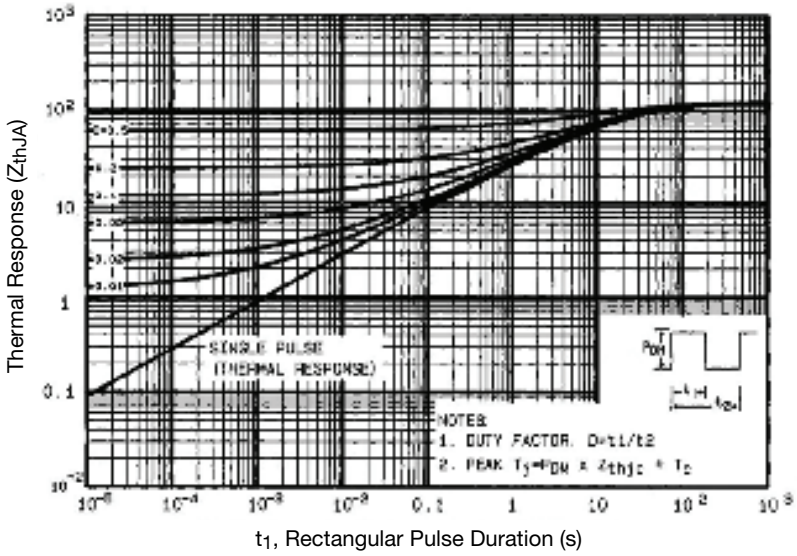


Fig. 9 - Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

For technical questions, contact: hvm@vishay.com

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

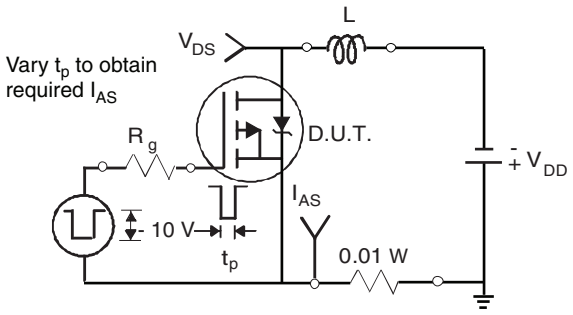


Fig. 12a - Unclamped Inductive Test Circuit

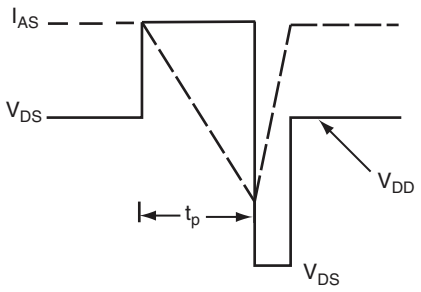


Fig. 12b - Unclamped Inductive Waveforms

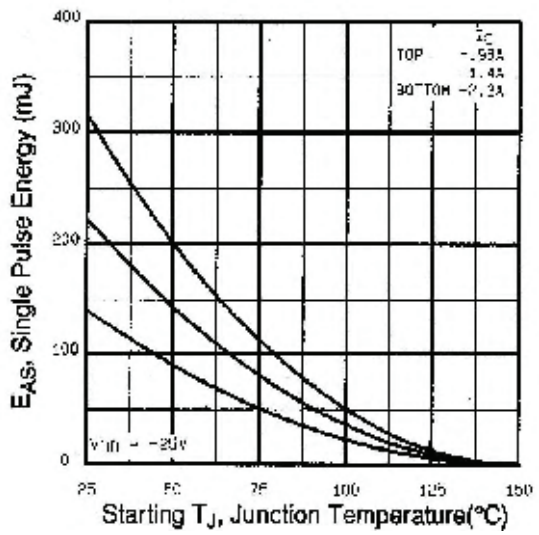


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

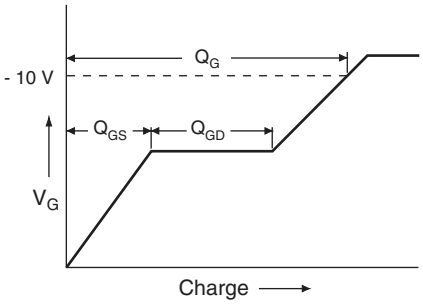


Fig. 13a - Basic Gate Charge Waveform

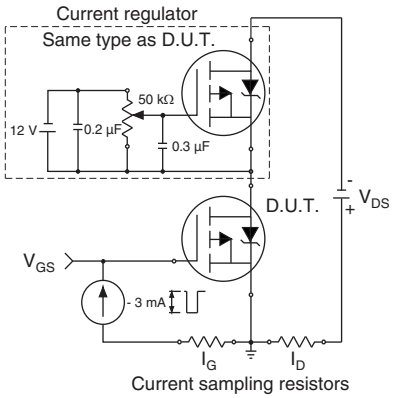
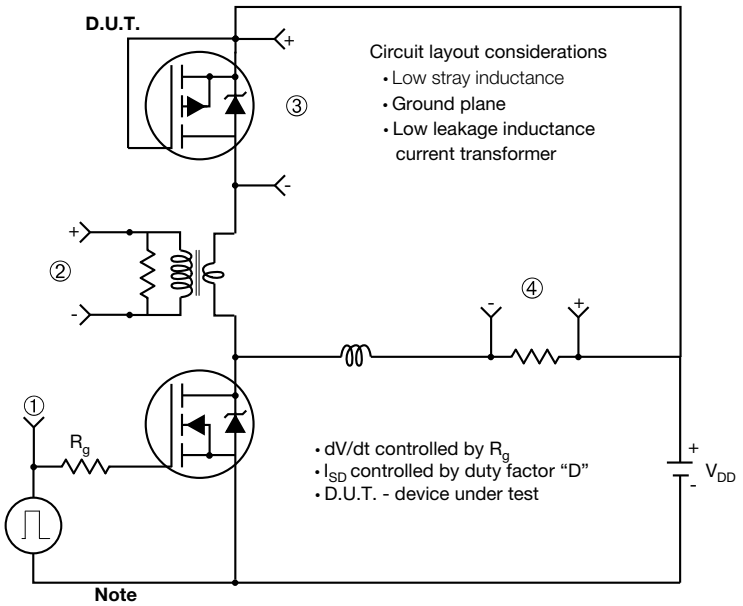


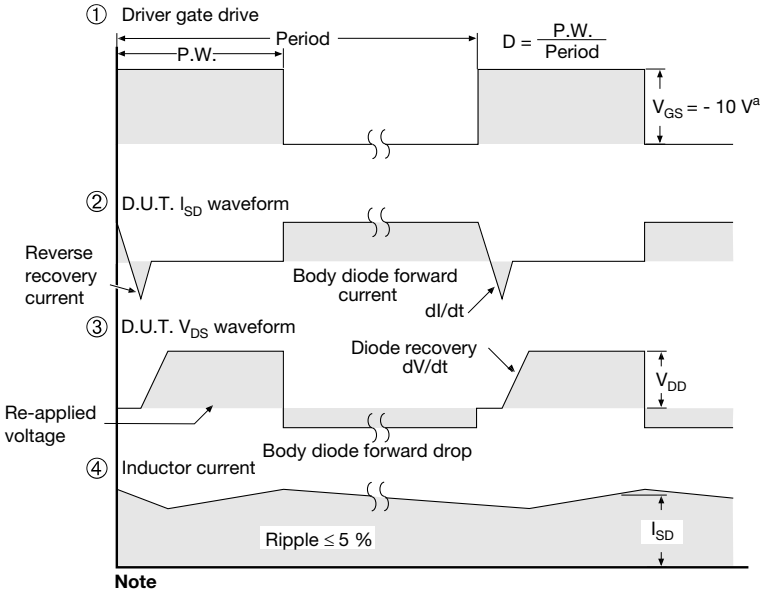
Fig. 13b - Gate Charge Test Circuit

For technical questions, contact: hvm@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

Peak Diode Recovery dV/dt Test Circuit



Note
• Compliment N-Channel of D.U.T. for driver



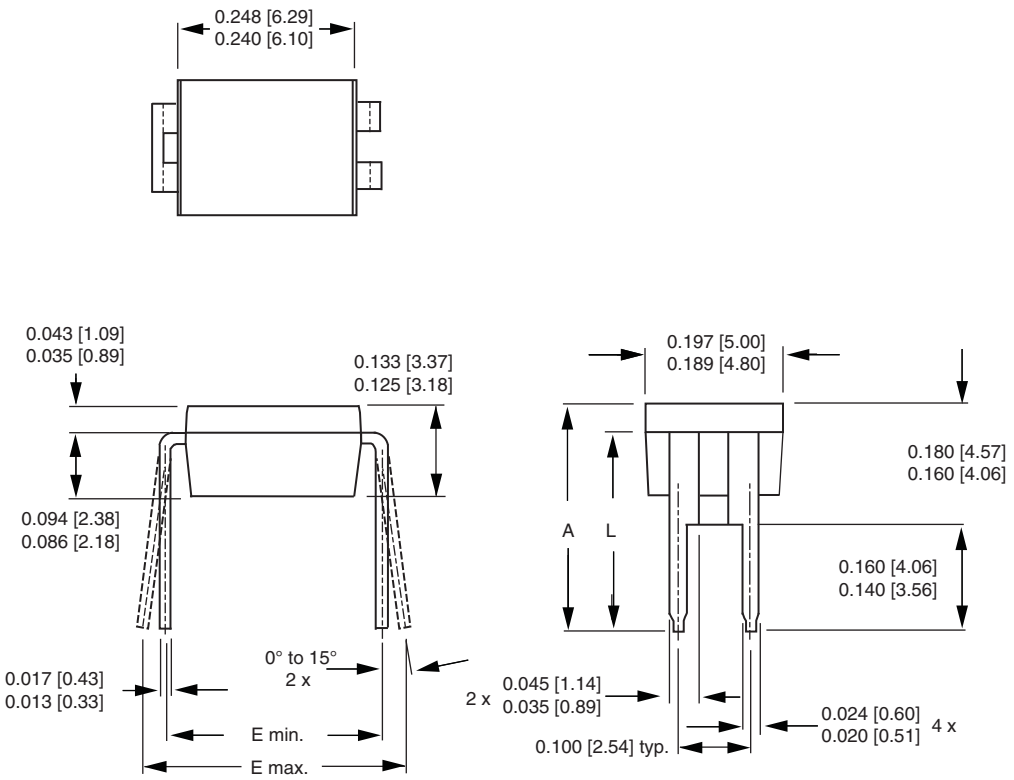
Note
a. V_{GS} = - 5 V for logic level and - 3 V drive devices

Fig. 10 - For P-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91136.

For technical questions, contact: hvm@vishay.com
THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

HVM DIP (High voltage)



	INCHES		MILLIMETERS	
DIM.	**MIN.**	**MAX.**	**MIN.**	**MAX.**
A	0.310	0.330	7.87	8.38
E	0.300	0.425	7.62	10.79
L	0.270	0.290	6.86	7.36
ECN: X10-0386-Rev. B, 06-Sep-10 DWG: 5974				

Note

1. Package length does not include mold flash, protrusions or gate burrs. Package width does not include interlead flash or protrusions.

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2026 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000